TOSHIBA Field-Effect Transistor Silicon N Channel MOS Type

SSM3K7002F

High-Speed Switching Applications Analog Switch Applications

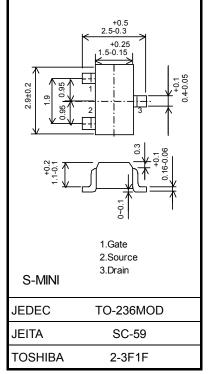
- Small package
 - Low ON-resistance $(@V_{GS} = 4.5 V)$

: $R_{on} = 3.2 \Omega (max) (@V_{GS} = 5 V)$

: $R_{on} = 3.0 \Omega (max) (@V_{GS} = 10 V)$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V _{DS}	60	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC	۱ _D	200	mA	
	Pulse	I _{DP}	800		
Drain power dissipation (Ta = 25° C)		PD	200	mW	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	



Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Weight: 0.012 g (typ.)

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

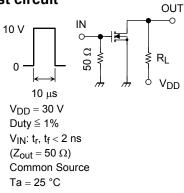
Electrical Characteristics (Ta = 25°C)

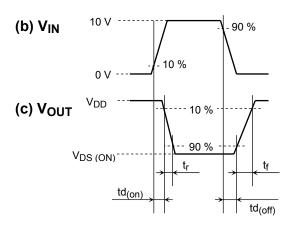
Characteristics		Symbol	Test Condition	Min	Тур	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS}=\pm20~V,~V_{DS}=0$	_	—	± 10	μA
Drain-source breakdown voltage		V (BR) DSS	I _D = 0.1 mA, V _{GS} = 0	60	_		V
Drain cutoff current		I _{DSS}	$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0$	_	_	1	μA
Gate threshold vo	ltage	V _{th}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 0.25 \text{ mA}$	1.0	_	2.5	V
Forward transfer a	admittance	Y _{fs}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 200 \text{ mA}$	170	_		mS
Drain-source ON-resistance		R _{DS} (ON)	I _D = 500 mA, V _{GS} = 10 V		2.0	3.0	Ω
			I _D = 100 mA, V _{GS} = 5 V		2.1	3.2	
			$I_D = 100 \text{ mA}, V_{GS} = 4.5 \text{ V}$		2.2	3.3	
Input capacitance		C _{iss}			17		pF
Reverse transfer capacitance		C _{rss}	V _{DS} = 25 V, V _{GS} = 0, f = 1 MHz		1.4		pF
Output capacitance		C _{oss}			5.8		pF
Switching time	Turn-on delay time	td _(on)	V _{DD} = 30 V , I _D = 200 mA ,		2.4	4.0	ns
	Turn-off delay time	td _(off)	$V_{GS} = 0$ to 10 V		26	40	

Unit: mm

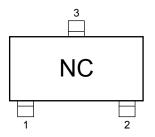
Switching Time Test Circuit

(a) Test circuit

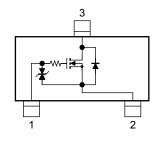




Marking



Equivalent Circuit (top view)



Precaution

 V_{th} can be expressed as the voltage between gate and source when the low operating current value is I_D = 0.25 mA for this product. For normal switching operation, $V_{GS\ (on)}$ requires a higher voltage than V_{th} and $V_{GS\ (off)}$ requires a lower voltage than V_{th} .

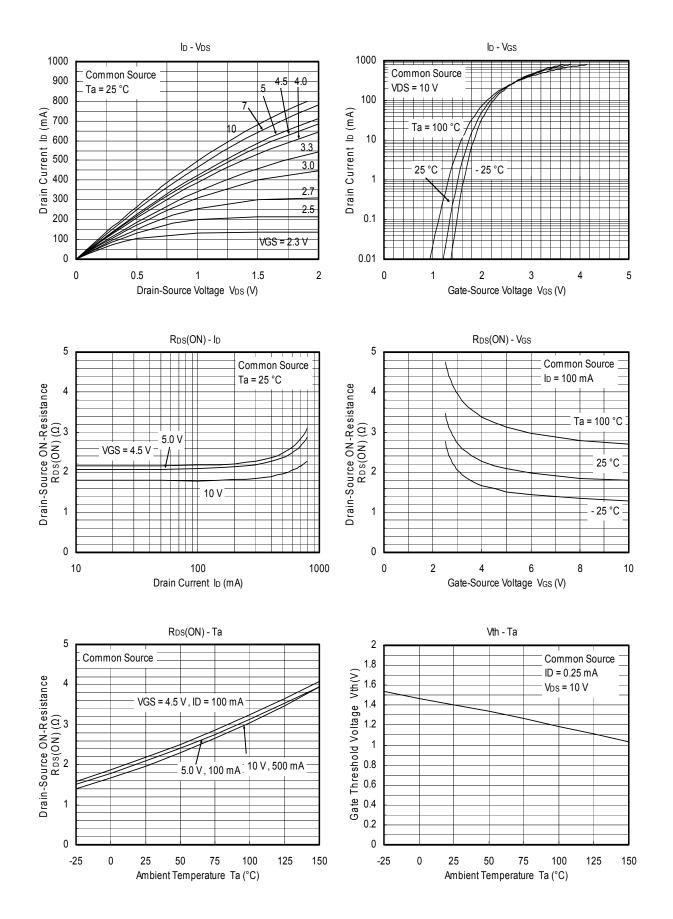
(The relationship can be established as follows: V_{GS (off)} < V_{th} < V_{GS (on).})

Take this into consideration when using the device.

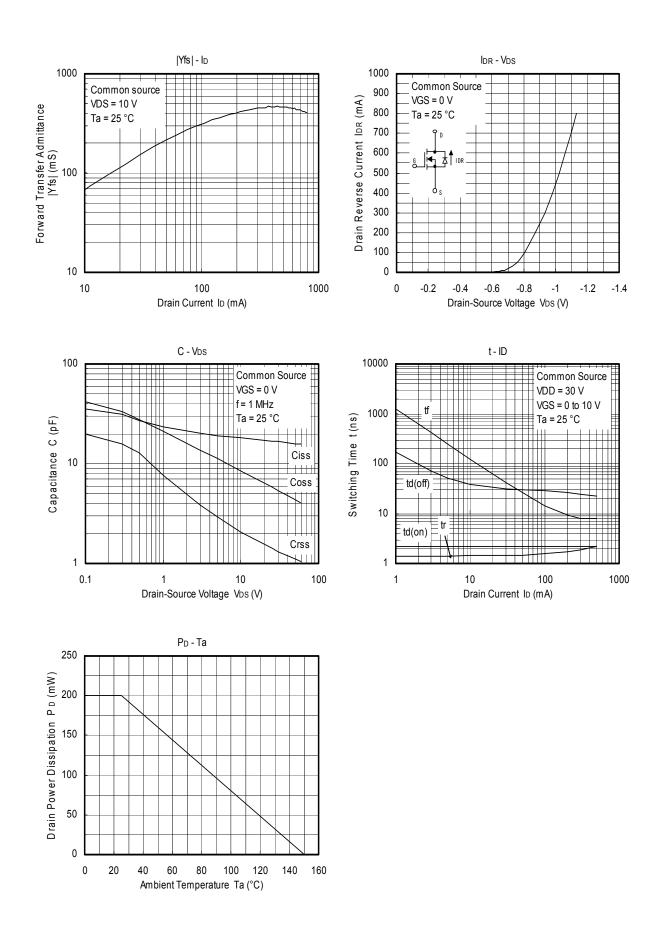
Handling Precaution

When handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.

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20070701-EN GENERAL

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